TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM5867-8UL

FEATURES

- HIGH POWER
 P1dB=39.5dBm at 5.85GHz to 6.75GHz
- BROAD BAND INTERNALLY MATCHED FET

■ HIGH GAIN

■ HERMETICALLY SEALED PACKAGE

G1dB=10.0dB at 5.85GHz to 6.75GHz

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB	101	dBm	38.5	39.5	
Compression Point						
Power Gain at 1dB Gain	G1dB	VDS= 10V	dB	9.0	10.0	
Compression Point		IDSset=1.8A f = 5.85GHz to 6.75GHz				
Drain Current	IDS1		Α		2.2	2.6
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%	_	36	
3rd Order Intermodulation	IM3	Two-Tone Test	dBc	-44	-47	_
Distortion		Po= 28.5dBm				
Drain Current	IDS2	(Single Carrier Level)	Α		2.2	2.6
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C			80

Recommended gate resistance(Rg) : Rg= 150 Ω (MAX.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	mS		1800	
		IDS= 3.0A				
Pinch-off Voltage	VGSoff	VDS= 3V	V	-1.0	-2.5	-4.0
		IDS= 30mA				
Saturated Drain Current	IDSS	VDS= 3V	Α		5.2	
		VGS= 0V				
Gate-Source Breakdown	VGSO	IGS= -100μA	V	-5		
Voltage						
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		2.5	3.5

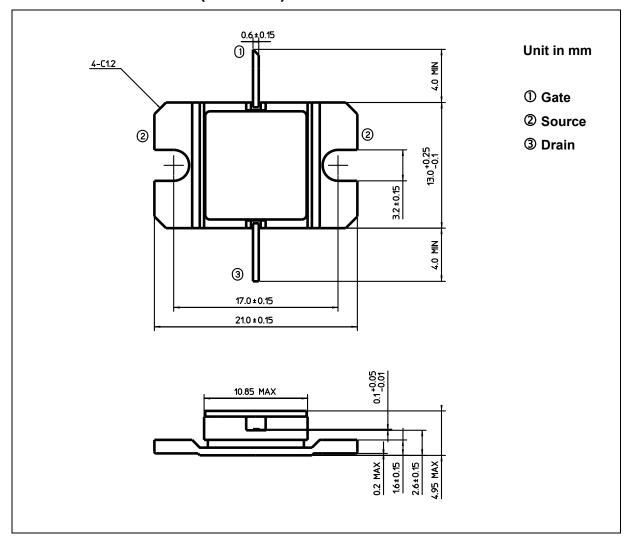
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	7.0
Total Power Dissipation (Tc= 25 °C)	PT	W	42.9
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11D1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.